

CLAIMS

Amend the claims as set forth below.

Claims 1.-8. (Cancelled)

9. (Currently amended) A low defectivity method for chemical mechanical planarization of a substrate comprised of dielectric material, the method comprising the steps of:

- i. providing a substrate comprised of dielectric material in contact with a polishing pad;
- ii. providing a composition for chemical mechanical planarization comprising a) an abrasive; b) a fluoride salt; and c) an acetylenic alcohol; and
- iii. polishing the substrate with the composition to effect at least partial planarization of the substrate;

wherein the acetylenic alcohol of the composition has at least two hydroxyl substituents and wherein the method exhibits a substantially lower level of defectivity using the composition of step ii for step iii polishing in comparison to a composition absent components b) and c) of the step ii composition.

10. (Cancelled)

11. (Previously presented) The method of Claim 9 wherein the acetylenic alcohol of the composition is 2,4,7,9-tetramethyl-5-decyn-4,7-diol.

12. (Previously presented) The method of Claim 9 wherein the acetylenic alcohol of the composition is a C_4 - C_{22} alkyne.

13. (Previously presented) The method of Claim 12 wherein the acetylenic alcohol of the composition is a C_{12} - C_{16} alkyne.

14. (Previously presented) The method of Claim 9 wherein the abrasive of the composition is a colloidal abrasive.

15. (Previously presented) The method of Claim 14 wherein the colloidal abrasive is colloidal silica.

16. (Previously presented) The method of Claim 9 wherein the fluoride salt of the composition is ammonium fluoride.

Claims 17.-18. (Cancelled)